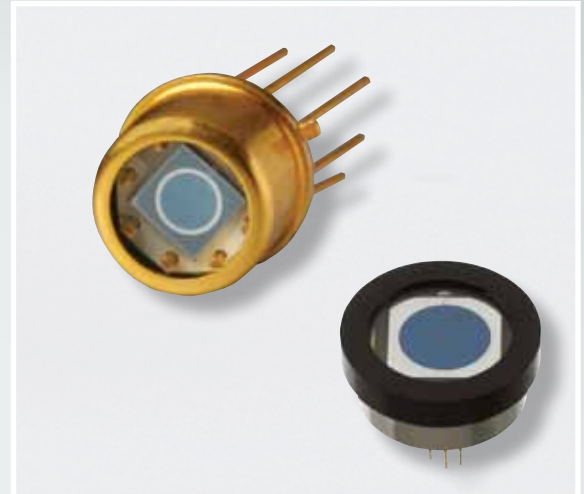


The Photop™ Series, combines a photodiode with an operational amplifier in the same package. Photops™ general-purpose detectors have a spectral range from either 350 nm to 1100 nm or 200 nm to 1100nm. They have an integrated package ensuring low noise output under a variety of operating conditions. These op-amps are specifically selected by OSI Optoelectronics engineers for compatibility to our photodiodes. Among many of these specific parameters are low noise, low drift and capability of supporting a variety of gains and bandwidths determined by the external feedback components. Operation from DC level to several MHz is possible in an either unbiased configuration for low speed, low drift applications or biased for faster response time.

Any modification of the above devices is possible. The modifications can be simply adding a bandpass optical filter, integration of additional chip (hybrid) components inside the same package, utilizing a different op-amp, photodetector replacement, modified package design and / or mount on PCB or ceramic.



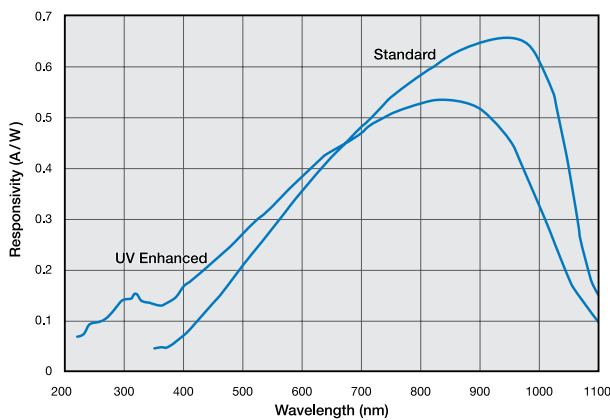
APPLICATIONS

- General Purpose Light Detection
- Laser Power Monitoring
- Medical Analysis
- Laser Communications
- Bar Code Readers
- Industrial Control Sensors
- Pollution Monitoring
- Guidance Systems
- Colorimeter

FEATURES

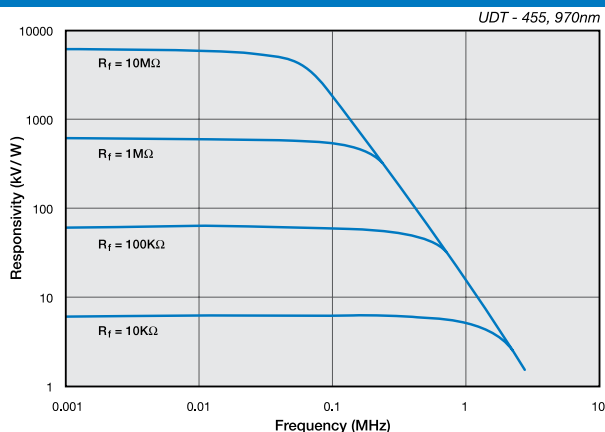
- Detector/Amplifier Combined
- Adjustable Gain/Bandwidth
- Low Noise
- Wide Bandwidth
- DIP Package
- Large Active Area

Typical Spectral Response

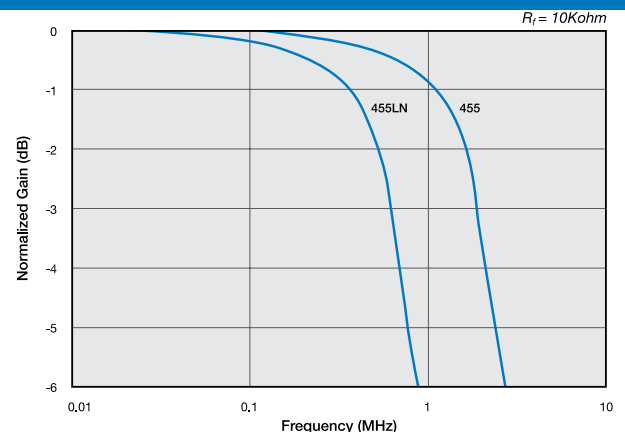


For your specific requirements, contact one of our Applications Engineers.

Typical Responsivity vs. Frequency



Typical Gain vs. Frequency



Photops™ (Photodiode Specifications)

Typical Electro-Optical Specifications at T_A=23°C

Model Number	Active Area		Responsivity (A/W)				Capacitance (pF)		Dark Current (nA)		Shunt Resistance (MΩ)	NEP (W/√Hz)		Reverse Voltage (V)	Temp.* Range (°C)		Package Style
	Area (mm ²)	Dimension (mm)	254 nm		970 nm		0 V	-10 V	-10 V			0 V	-10 V		Operating	Storage	
			min.	typ.	min.	typ.	typ.	typ.	typ.	max.	typ.	typ.	max.				
350-1100 nm Spectral Range																	
UDT-455	5.1	2.54 φ	---	0.60	0.65	85	15	0.25	3	---	---	1.4 e -14	30**	0 ~ + 70	- 30 ~ + 100		30 / TO-5
OSI-515#																	31 / TO-8
UDT-020D																	32 / Special
UDT-555D	100	11.3 φ				1500	300	2	25			3.9 e -14					
200-1100 nm Spectral Range																	
UDT-455UV	5.1	2.54 φ	0.10	0.14	---	300		---		100	9.2 e -14	---	5**	0 ~ + 70	- 30 ~ + 100		30 / TO-5
OSI-020UV	16	4.57 φ				1000				50	1.3 e -13						31 / TO-8
UDT-055UV	50	7.98 φ				2500				20	2.1 e -13						32 / Special
UDT-555UV	100	11.3 φ				4500				10	2.9 e -13						32 / Special
UDT-555UV/LN**																	

Operational Amplifier Specifications Electro-Optical Specifications at T_A=23 °C

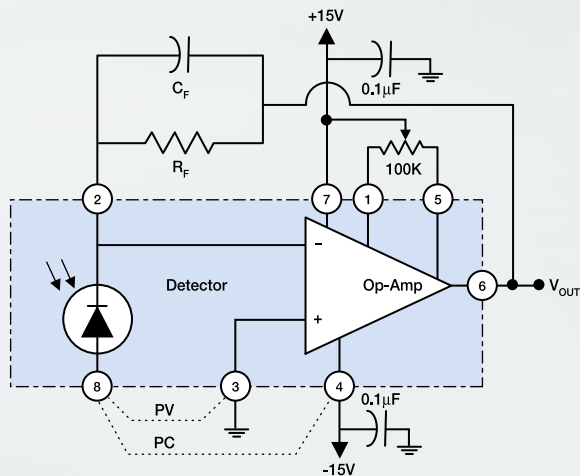
Model Number	Supply Voltage			Quiescent Supply Current (mA)		Input Offset Voltage		Temp. Coefficient Input Offset Voltage		Input Bias Current		Gain Bandwidth Product		Slew Rate		Open Loop Gain, DC		Input Noise Voltage		Input Noise Current
				± 15 V		mV		μV / °C		pA		MHz		V / μs		V / mV		100 Hz	1 kHz	1 kHz
	min.	typ.	max.	typ.	max.	typ.	max.	typ.	max.	typ.	max.	min.	typ.	min.	typ.	min.	typ.	typ.	typ.	typ.
UDT-455	---	±15	±18	2.8	5.0	0.5	3	4	30	±80	±400	3.0	5.4	5	9	50	200	20	15	10
UDT-455UV																				
UDT-020D																				
OSI-020UV	---	±15	±18	1.8	2	0.03	0.12	0.35	1	0.5	20	---	5.1	---	20	1000	2000	5.8	5.1	0.8
OSI-515*	---	±15	±18	6.5	7.2	1	3	10	---	±15	±40	23	26	125	140	3	6.3	---	12	10
UDT-555UV/LN	---	±15	±18	2.5	3.5	0.1	0.5	±2	±5	±0.8	±2	---	2	1	2	501	1778	15	8	0.5
UDT-055UV	---	±15	±22	2.7	4.0	0.4	1	3	10	±40	±200	3.5	5.7	7.5	11	75	220	20	15	10
UDT-555D																				
UDT-555UV																				

¶ For mechanical drawings please refer to pages 61 thru 73.

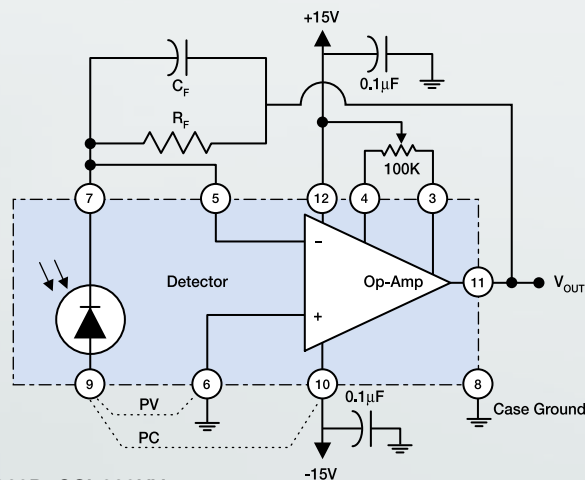
** LN – Series Devices are to be used with a 0V Bias.

* Non-Condensing temperature and Storage Range, Non-Condensing Environment.

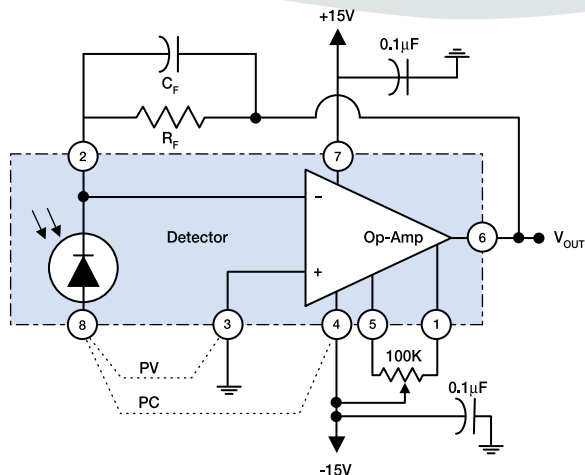
OSI-515 replaces UDT-455HS



UDT-455,
UDT-555D, 555UV, 055UV
OSI-515: pin 1 & 5 are N/C
(No offset adjustment needed).



UDT-020D, OSI-020UV



UDT-555UV/LN

The output voltage is proportional to the light intensity of the light and is given by:

$$V_{OUT} = I_P \times R_F \quad (1)$$

$$= (P \times R_\lambda) \times R_F$$

Frequency Response (Photodiode/Amplifier Combination)

The frequency response of the photodiode / amplifier combination is determined by the characteristics of the photodiode, pre-amplifier as well as the feedback resistor (R_F) and feedback capacitor (C_F). For a known gain, (R_F), the 3dB frequency response of the detector/pre-amp combination is given by:

$$f_{3dB} = \frac{1}{2\pi C_F R_F} \quad (2)$$

However, the desired frequency response is limited by the Gain Bandwidth Product (GBP) of the op-amp. In order to have a stable output, the values of the R_F and C_F must be chosen such that the 3dB frequency response of the detector / pre-amp combination, be less than the maximum frequency of the op-amp, i.e. $f_{3dB} \leq f_{max}$.

$$f_{max} = \sqrt{\frac{GBP}{2\pi R_F (C_F + C_J + C_A)}} \quad (3)$$

where C_A is the amplifier input capacitance.

In conclusion, an example for frequency response calculations, is given below. For a gain of 10^3 , an operating frequency of 100 Hz, and an op-amp with GBP of 5 MHz:

$$C_F = \frac{1}{2\pi f_{3dB} R_F} = 15.9pF \quad (4)$$

Thus, for $C_F = 15.9$ pF, $C_J = 15$ pF and $C_A = 7$ pF, f_{max} is about 14.5 kHz. Hence, the circuit is stable since $f_{3dB} \leq f_{max}$.

For more detailed application specific discussions and further reading, refer to the APPLICATION NOTES INDEX in the catalog.

Note: The shaded boxes represent the Photop™ components and their connections. The components outside the boxes are typical

AVOID DIRECT LIGHT

Since the spectral response of silicon photodiode includes the visible light region, care must be taken to avoid photodiode exposure to high ambient light levels, particularly from tungsten sources or sunlight. During shipment from OSI Optoelectronics, your photodiodes are packaged in opaque, padded containers to avoid ambient light exposure and damage due to shock from dropping or jarring.

AVOID SHARP PHYSICAL SHOCK

Photodiodes can be rendered inoperable if dropped or sharply jarred. The wire bonds are delicate and can become separated from the photodiode's bonding pads when the detector is dropped or otherwise receives a sharp physical blow.

CLEAN WINDOWS WITH OPTICAL GRADE CLOTH / TISSUE

Most windows on OSI Optoelectronics photodiodes are either silicon or quartz. They should be cleaned with isopropyl alcohol and a soft (optical grade) pad.

OBSERVE STORAGE TEMPERATURES AND HUMIDITY LEVELS

Photodiode exposure to extreme high or low storage temperatures can affect the subsequent performance of a silicon photodiode. Storage temperature guidelines are presented in the photodiode performance specifications of this catalog. Please maintain a non-condensing environment for optimum performance and lifetime.

OBSERVE ELECTROSTATIC DISCHARGE (ESD) PRECAUTIONS

OSI Optoelectronics photodiodes, especially with IC devices (e.g. Photops) are considered ESD sensitive. The photodiodes are shipped in ESD protective packaging. When unpacking and using these products, anti-ESD precautions should be observed.

DO NOT EXPOSE PHOTODIODES TO HARSH CHEMICALS

Photodiode packages and/or operation may be impaired if exposed to CHLOROTHENE, THINNER, ACETONE, or TRICHLOROETHYLENE.

INSTALL WITH CARE

Most photodiodes in this catalog are provided with wire or pin leads for installation in circuit boards or sockets. Observe the soldering temperatures and conditions specified below:

Soldering Iron:	Soldering 30 W or less Temperature at tip of iron 300°C or lower.
Dip Soldering:	Bath Temperature: 260±5°C. Immersion Time: within 5 Sec. Soldering Time: within 3 Sec.
Vapor Phase Soldering:	DO NOT USE
Reflow Soldering:	DO NOT USE

Photodiodes in plastic packages should be given special care. Clear plastic packages are more sensitive to environmental stress than those of black plastic. Storing devices in high humidity can present problems when soldering. Since the rapid heating during soldering stresses the wire bonds and can cause wire to bonding pad separation, it is recommended that devices in plastic packages to be baked for 24 hours at 85°C.

The leads on the photodiode **SHOULD NOT BE FORMED**. If your application requires lead spacing modification, please contact OSI Optoelectronics Applications group at (310)978-0516 before forming a product's leads. Product warranties could be voided.



*Most of our standard catalog products are RoHS Compliant. Please contact us for details

Mechanical Drawings

Mechanical Specifications and Die Topography

1. Parameter Definitions:

A = Distance from top of chip to top of glass.

a = Photodiode Anode.

B = Distance from top of glass to bottom of case.

c = Photodiode Cathode

(Note: cathode is common to case in metal package products unless otherwise noted).

W = Window Diameter.

F.O.V. = Filed of View (see definition below).

2. Dimensions are in inches (1 inch = 25.4 mm).

3. Pin diameters are 0.018 ± 0.002 " unless otherwise specified.

4. Tolerances (unless otherwise noted)

General: $0.XX \pm 0.01$ "

$0.XXX \pm 0.005$ "

Chip Centering: ± 0.010 "

Dimension 'A': ± 0.015 "

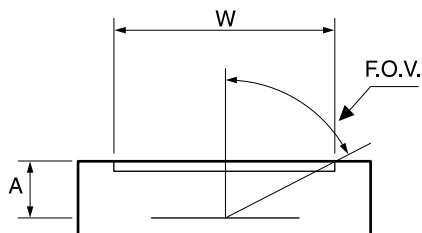
5. Windows

All '**UV**' Enhanced products are provided with QUARTZ glass windows, 0.027 ± 0.002 " thick.

All '**XUV**' products are provided with removable windows.

All '**DLS**' PSD products are provided with A/R coated glass windows.

All '**FIL**' photoconductive and photovoltaic products are epoxy filled instead of glass windows.



$$F.O.V. = \tan^{-1} \left(\frac{W}{2A} \right)$$

For Further Assistance
Please Call One of Our Experienced
Sales and Applications Engineers

310-978-0516

OSI Optoelectronics
An OSI Systems Company

- Or -

visit our website at

www.osioptoelectronics.com